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[54] **ARRANGEMENT FOR TREATMENT OF WAFER-SHAPED ARTICLES, PARTICULARLY SILICON WAFERS**

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[58] **Field of Search** 134/95.3, 198, 134/172, 148, 153; 118/320, 323, 52

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[57] **ABSTRACT**

In order to remove, after treatment of wafer-shaped articles (**2**), preferably a silicon wafer, with a treatment medium, preferably with an etching fluid, on the bottom of wafer-shaped article (**2**), i.e. the side facing chuck (**1**) for wafer-shaped article (**2**), residual treatment medium adhering in its edge area, there is nozzle (**20**) from which flushing liquid, preferably deionized water, can be sprayed onto the outside edge of article (**2**) and between chuck (**1**) and wafer-shaped article (**2**). The flushing liquid, which penetrates more or less deeply, depending on the pressure with which the flushing liquid emerges from nozzle (**20**) and depending on the alignment of nozzle (**20**) relative to wafer-shaped article (**2**), is flung off again by the rotation of wafer-shaped article (**2**) and in doing so entrains residues of treatment medium. For optimum action the alignment of nozzle (**20**) can be changed relative to edge (**16**) of wafer-shaped article (**2**).

8 Claims, 2 Drawing Sheets